

December 16, 2004

Renesas builds world's smallest MRAM.

On December 14, 2004 Renesas Technology Corporation announced at the 2004 IEEE International Electron Device Meeting in San Francisco, California that it has fabricated a prototype 1-Mbit Magnetoresistive Random Access Memory ("MRAM") chip with what it says is "the world's smallest memory cell size of 0.81µm2." According to the press release, Renesas developed the MRAM technology for system-on-a-chip use.

Cypress Semiconductor Corporation (NYSE: CY, \$11.13) has failed to create a working MRAM chip using NVE Corporation's (NASDAQ: NVEC, \$27.98) alleged intellectual property since at least April 2002. Cypress' most recent disclosures state that its proposed 256-Kbit MRAM design employs a whopping 24µ2 cell. The Renesas prototype MRAM chip has a cell that is 29.6 times smaller than Cypress' design.

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NVE's MRAM IP claims are based on a forty-year-old IBM patent that is now in wide and royalty-free use in memory chips worldwide. (Click here for a complete analysis of NVE's MRAM IP claims.) Contrary to its claims, NVE is not and has never been involved with the development of MRAM or any invention needed to create an MRAM memory cell. (Click for a detailed description of MRAM's development and its developers.)

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